

Peter Zaumseil

List of Publications by Year in descending order

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18
papers

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933447

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docs citations

18
times ranked

391
citing authors

#	ARTICLE	IF	CITATIONS
1	Temperature dependence of strain-phonon coefficient in epitaxial Ge/Si(001): A comprehensive analysis. Journal of Raman Spectroscopy, 2020, 51, 989-996.	2.5	20
2	Composition analysis and transition energies of ultrathin Sn-rich GeSn quantum wells. Physical Review Materials, 2020, 4, .	2.4	10
3	Morphological evolution of Ge/Si nano-strips driven by Rayleigh-like instability. Applied Physics Letters, 2018, 112, 022101.	3.3	10
4	Gate stack and Ni(SiGeSn) metal contacts formation on low bandgap strained (Si)Ge(Sn) semiconductors. , 2018, , .		2
5	Photoluminescence from GeSn nano-heterostructures. Nanotechnology, 2018, 29, 415702.	2.6	9
6	Structural analysis of a phosphide-based epitaxial structure with a buried oxidized AlAs sacrificial layer. Journal of Applied Physics, 2017, 121, 215303.	2.5	0
7	Schottky barrier tuning <i>via</i> dopant segregation in NiGeSn-GeSn contacts. Journal of Applied Physics, 2017, 121, .	2.5	20
8	Dislocation-free Ge Nano-crystals via Pattern Independent Selective Ge Heteroepitaxy on Si Nano-Tip Wafers. Scientific Reports, 2016, 6, 22709.	3.3	25
9	Selective growth of fully relaxed GeSn nano-islands by nanoheteroepitaxy on patterned Si(001). Applied Physics Letters, 2016, 109, .	3.3	10
10	Characterization of reclaimed GaAs substrates and investigation of reuse for thin film InGaAlP LED epitaxial growth. Journal of Applied Physics, 2016, 120, 045301.	2.5	7
11	Photodetection in Hybrid Single-Layer Graphene/Fully Coherent Germanium Island Nanostructures Selectively Grown on Silicon Nanotip Patterns. ACS Applied Materials & Interfaces, 2016, 8, 2017-2026.	8.0	32
12	Sn migration control at high temperature due to high deposition speed for forming high-quality GeSn layer. Applied Physics Express, 2016, 9, 031201.	2.4	11
13	Fabrication of GeSn-multiple quantum wells by overgrowth of Sn on Ge by using molecular beam epitaxy. Applied Physics Letters, 2015, 107, .	3.3	12
14	Ternary and quaternary Ni(Si)Ge(Sn) contact formation for highly strained Ge p- and n-MOSFETs. Semiconductor Science and Technology, 2015, 30, 055003.	2.0	28
15	Fully coherent growth of Ge on free-standing Si(001) nanomesas. Physical Review B, 2014, 89, .	3.2	32
16	Compliant Si nanostructures on SOI for Ge nanoheteroepitaxy- A case study for lattice mismatched semiconductor integration on Si(001). Journal of Applied Physics, 2012, 112, 043506.	2.5	13
17	About the strain state of different metal oxide layers epitaxially grown on Si(100). Journal Physics D: Applied Physics, 2011, 44, 055403.	2.8	12
18	A complex x-ray characterization of heteroepitaxial silicon/insulator/silicon(111) structures. Journal of Applied Physics, 2008, 104, .	2.5	16